 FORM PTO-1449 OFFICE OF PATENTS AND TRADEMARKS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	Atty. Docket No.: H26341 D2 (1139.1124104)	Serial No.: 10/617,892
	Applicant:	
	Ralph Johnson et al.	
	Filing Date July 11, 2003	Group Art: unknown

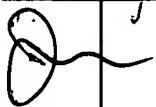
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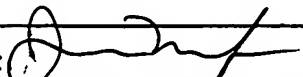
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EXAMINER: 	DATE CONSIDERED: 8/19/05
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

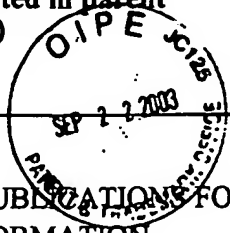
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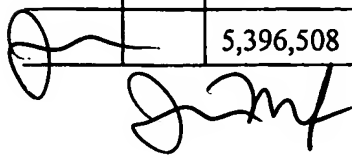
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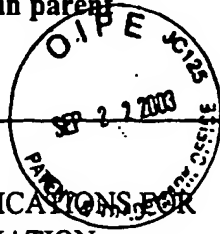
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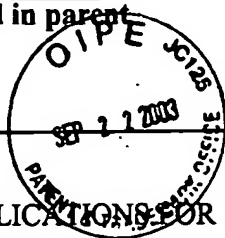
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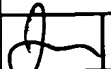
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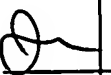




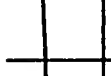




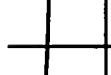

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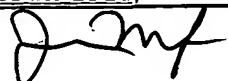
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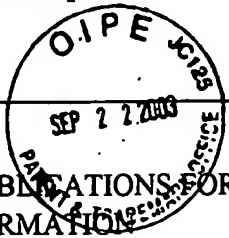
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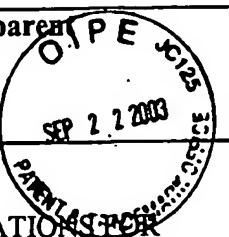
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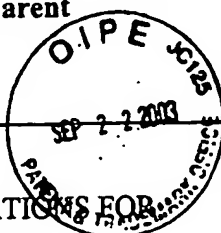
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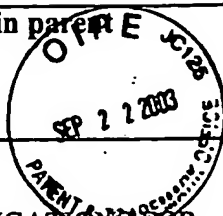
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